



8NM65A

Power MOSFET

8.0A, 650V N-CHANNEL POWER MOSFET

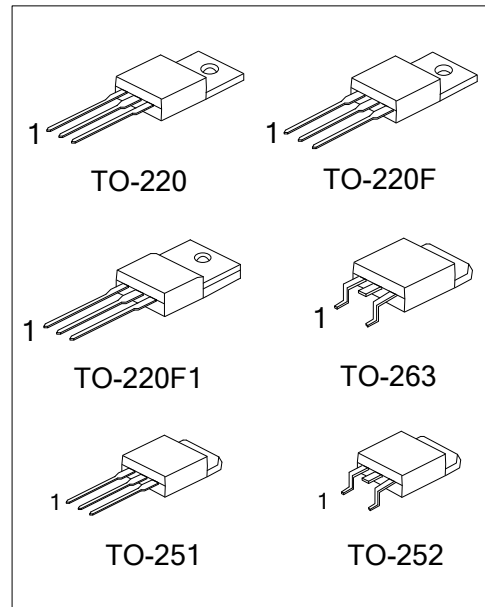
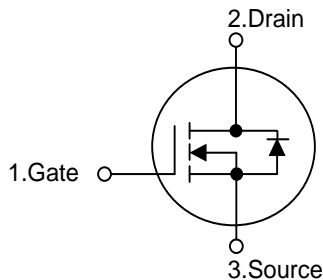
DESCRIPTION

The UTC **8NM65A** is a high voltage super junction MOSFET and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and have a high rugged avalanche characteristics. This power MOSFET is usually used at high speed switching applications in switching power supplies and adaptors.

FEATURES

- * $R_{DS(ON)} \leq 0.72 \Omega @ V_{GS} = 10V, I_D = 4.0A$
- * Fast Switching Capability
- * Improved dv/dt Capability, High Ruggedness

SYMBOL



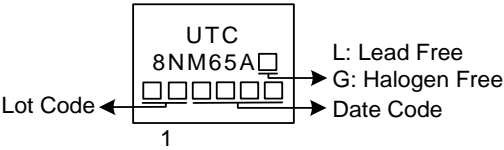
ORDERING INFORMATION

Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
8NM65AL-TA3-T	8NM65AG-TA3-T	TO-220	G	D	S	Tube
8NM65AL-TF1-T	8NM65AG-TF1-T	TO-220F1	G	D	S	Tube
8NM65AL-TF3-T	8NM65AG-TF3-T	TO-220F	G	D	S	Tube
8NM65AL-TM3-T	8NM65AG-TM3-T	TO-251	G	D	S	Tube
8NM65AL-TN3-R	8NM65AG-TN3-R	TO-252	G	D	S	Tape Reel
8NM65AL-TQ2-T	8NM65AG-TQ2-T	TO-263	G	D	S	Tube
8NM65AL-TQ2-R	8NM65AG-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>8NM65AG-TA3-T</p> <p>(1) Packing Type</p> <p>(2) Package Type</p> <p>(3) Green Package</p>	<p>(1) T: Tube, R: Tape Reel</p> <p>(2) TA3: TO-220, TF1: TO-220F1, TF3: TO-220F, TM3: TO-251, TN3: TO-252, TQ2: TO-263</p> <p>(3) G: Halogen Free and Lead Free, L: Lead Free</p>
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■ MARKING



■ ABSOLUTE MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	650	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	8.0	A
	Pulsed (Note 2)	I_{DM}	32	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	153.2	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	7.0	V/ns
Power Dissipation	TO-220/TO-263	P_D	76	W
	TO-220F/TO-220F1		28	W
	TO-251/TO-252		50	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3. $L=60\text{mH}$, $I_{AS}=2.26\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\ \Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD}\leq 8.0\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL DATA

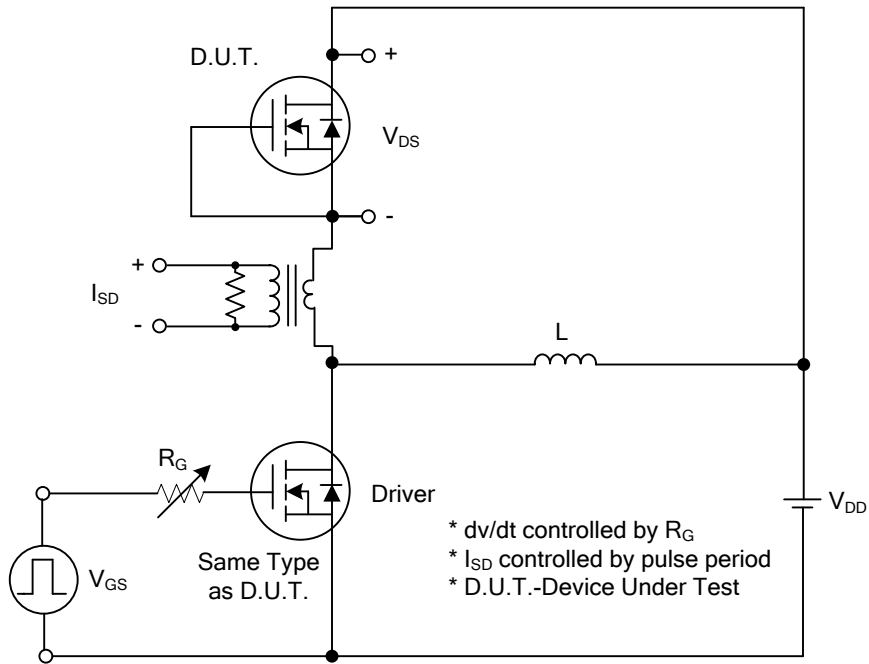
PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220/ TO-220F	θ_{JA}	62.5	$^\circ\text{C/W}$
	TO-220F1/TO-263			
	TO-251/TO-252			
Junction to Case	TO-220/TO-263	θ_{JC}	1.64	$^\circ\text{C/W}$
	TO-220F/TO-220F1		4.46	$^\circ\text{C/W}$
	TO-251/TO-252		2.5	$^\circ\text{C/W}$

■ ELECTRICAL CHARACTERISTICS (T_C=25°C, unless otherwise specified)

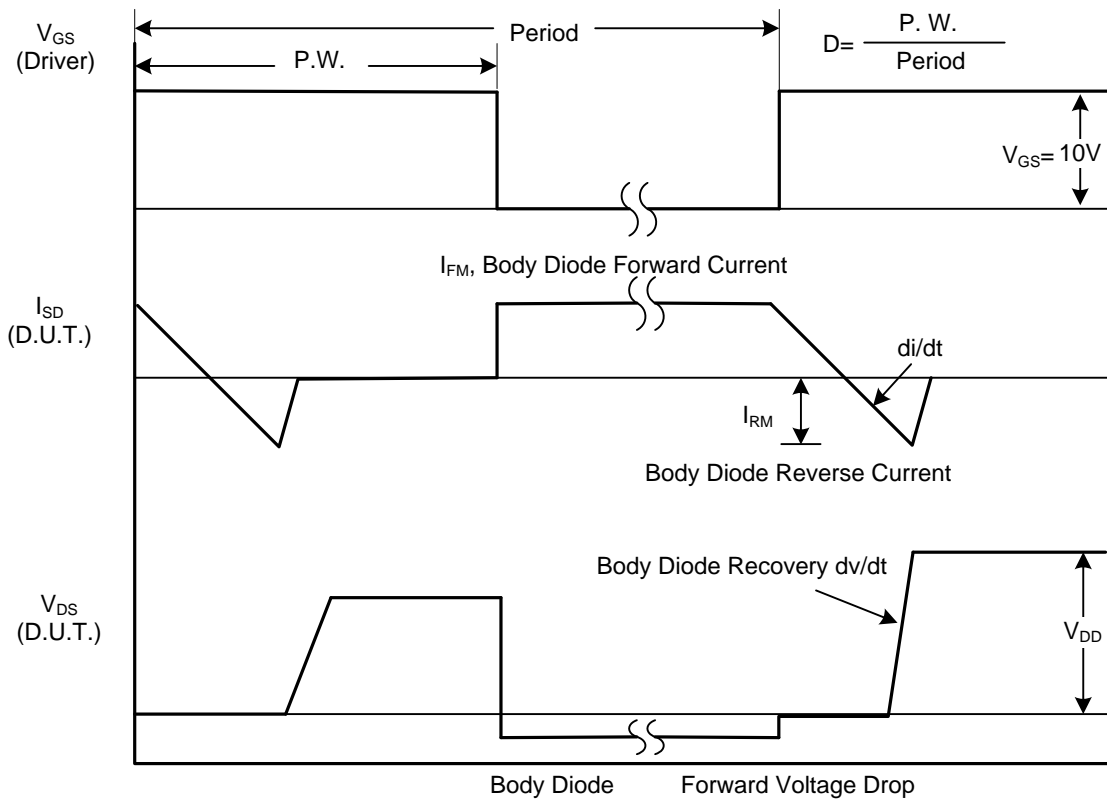
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, I _D = 250μA	650			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} = 650V, V _{GS} = 0V			10	μA
Gate- Source Leakage Current	Forward	I _{GSS}			100	nA
	Reverse					
		V _{GS} = -30V, V _{DS} = 0V			-100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250μA	2.5		4.5	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 4.0A			0.72	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1.0 MHz		472		pF
Output Capacitance	C _{OSS}			279		pF
Reverse Transfer Capacitance	C _{RSS}			22		pF
SWITCHING PARAMETERS						
Total Gate Charge (Note 1)	Q _G	V _{DS} =50V, V _{GS} =10V, I _D =1.3A, I _G =100μA (Note 1, 2)		19.8		nC
Gate to Source Charge	Q _{GS}			4.8		nC
Gate to Drain Charge	Q _{GD}			9.0		nC
Turn-on Delay Time (Note 1)	t _{D(ON)}	V _{DD} =30V, V _{GS} =10V, I _D =0.5A, R _G =25Ω (Note 1, 2)		43		ns
Rise Time	t _R			73		ns
Turn-off Delay Time	t _{D(OFF)}			166		ns
Fall-Time	t _F			63		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Pulsed Current	I _S				8	A
Drain-Source Diode Forward Voltage (Note 1)	I _{SM}				32	A
Maximum Body-Diode Continuous Current	V _{SD}	I _S =8.0A, V _{GS} =0V			1.4	V
Reverse Recovery Time (Note 1)	t _{rr}	I _S =8.0A, V _{GS} =0V di/dt=100A/μs		312		ns
Reverse Recovery Charge	Q _{rr}				3.69	

- Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.
 2. Essentially independent of operating temperature.

TEST CIRCUITS AND WAVEFORMS

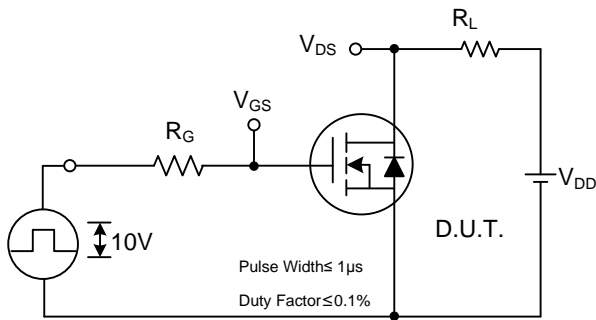


Peak Diode Recovery dv/dt Test Circuit

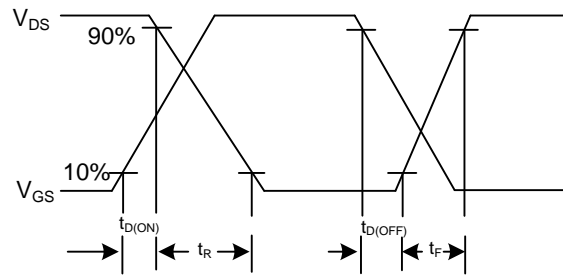


Peak Diode Recovery dv/dt Waveforms

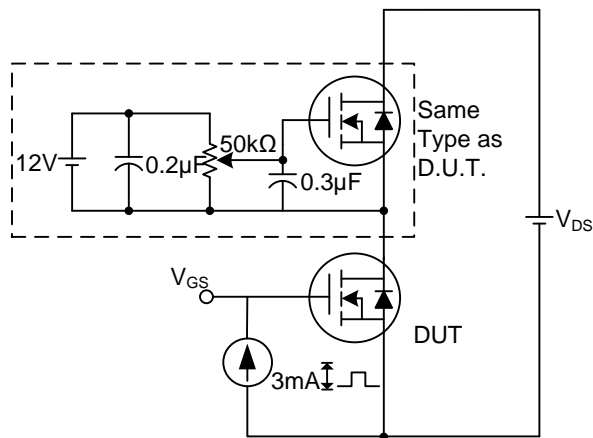
TEST CIRCUITS AND WAVEFORMS (Cont.)



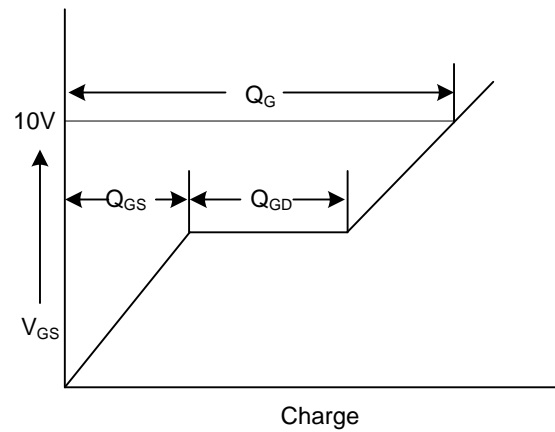
Switching Test Circuit



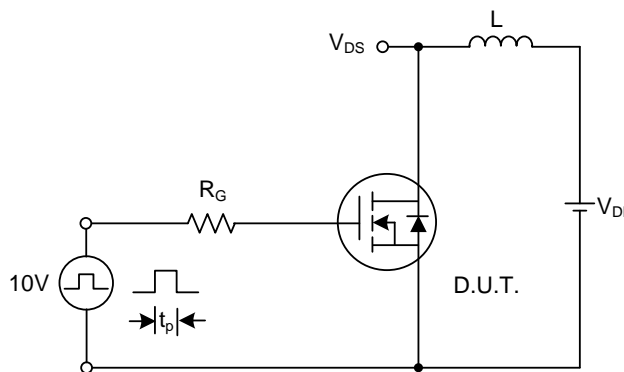
Switching Waveforms



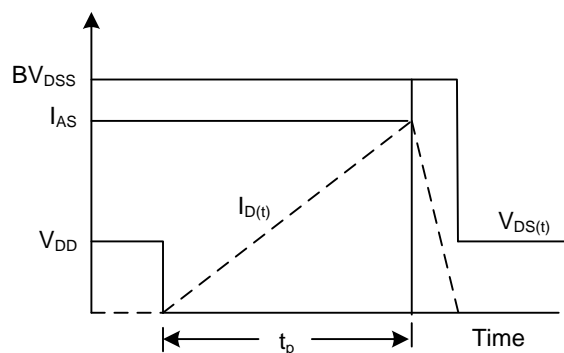
Gate Charge Test Circuit



Gate Charge Waveform

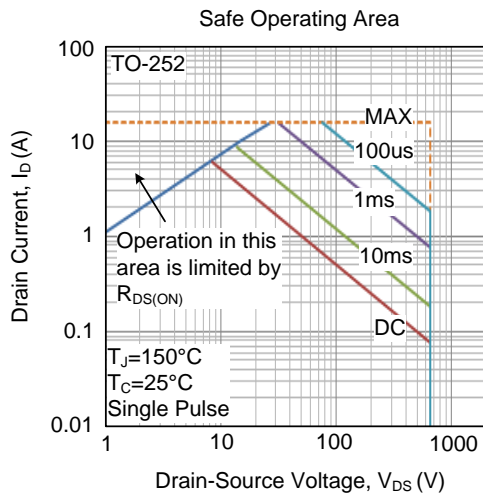


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS (Cont.)



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